

描述 / Descriptions

TO-220F 塑封封装 PNP 半导体三极管。Silicon PNP transistor in a TO-220F Plastic Package.

特征 / Features

低饱和压降,极好的直流电流特性,宽阔的安全工作区,与 2SD1833 互补。

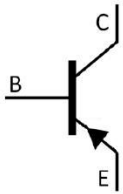
Low $V_{CE(sat)}$, excellent DC current gain characteristics, wide SOA, complements the 2SD1833.

用途 / Applications

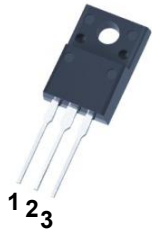
用于一般功率放大。

General power amplifier applications.

内部等效电路 / Equivalent Circuit



引脚排列 / Pinning



PIN1 : Base PIN 2 : Collector PIN 3 : Emitter

放大及印章代码 / h_{FE} Classifications & Marking

见印章说明。See Marking Instructions.

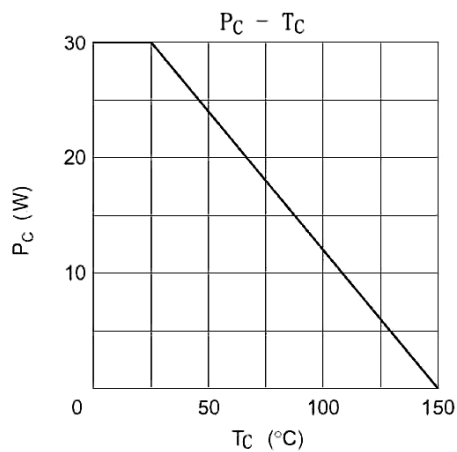
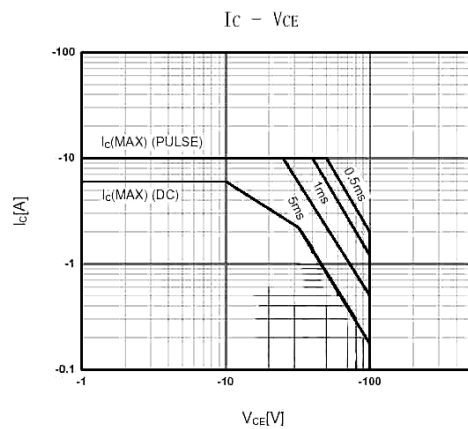
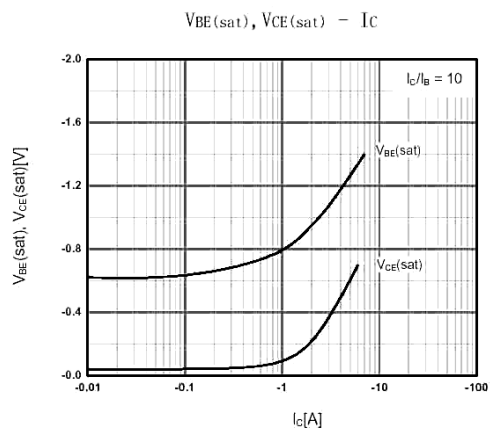
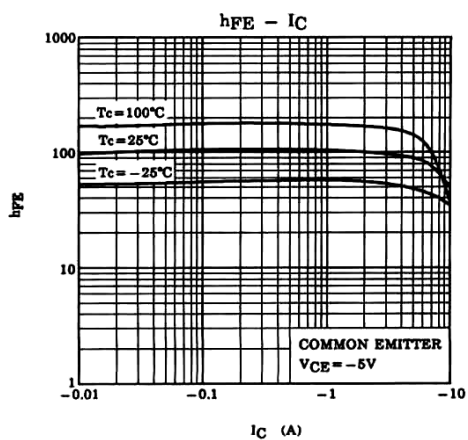
极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Collector to Base Voltage	V_{CBO}	-80	V
Collector to Emitter Voltage	V_{CEO}	-80	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-7.0	A
Collector Current – Continuous(Pulse)	I_{CP}	-10	A
Collector Power Dissipation	P_C	2.0	W
Collector Power Dissipation	$P_C(TC=25^{\circ}C)$	30	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=-50\mu A$ $I_E=0$	-80			V
Collector to Base Breakdown Voltage	V_{CEO}	$I_C=-1.0mA$ $I_B=0$	-80			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=-50\mu A$ $I_C=0$	-5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-80V$ $I_E=0$			-10	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-4.0V$ $I_C=0$			-10	μA
DC Current Gain	h_{FE}	$V_{CE}=-5.0V$ $I_C=-1.0A$	60		320	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-4.0A$ $I_B=-0.4A$			-1.0	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-4.0A$ $I_B=-0.4A$			-1.5	V
Transition Frequency	f_T	$V_{CE}=-5.0V$ $f=5.0MHz$ $I_E=0.5A$		12		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V$ $f=1.0MHz$ $I_E=0A$		200		pF

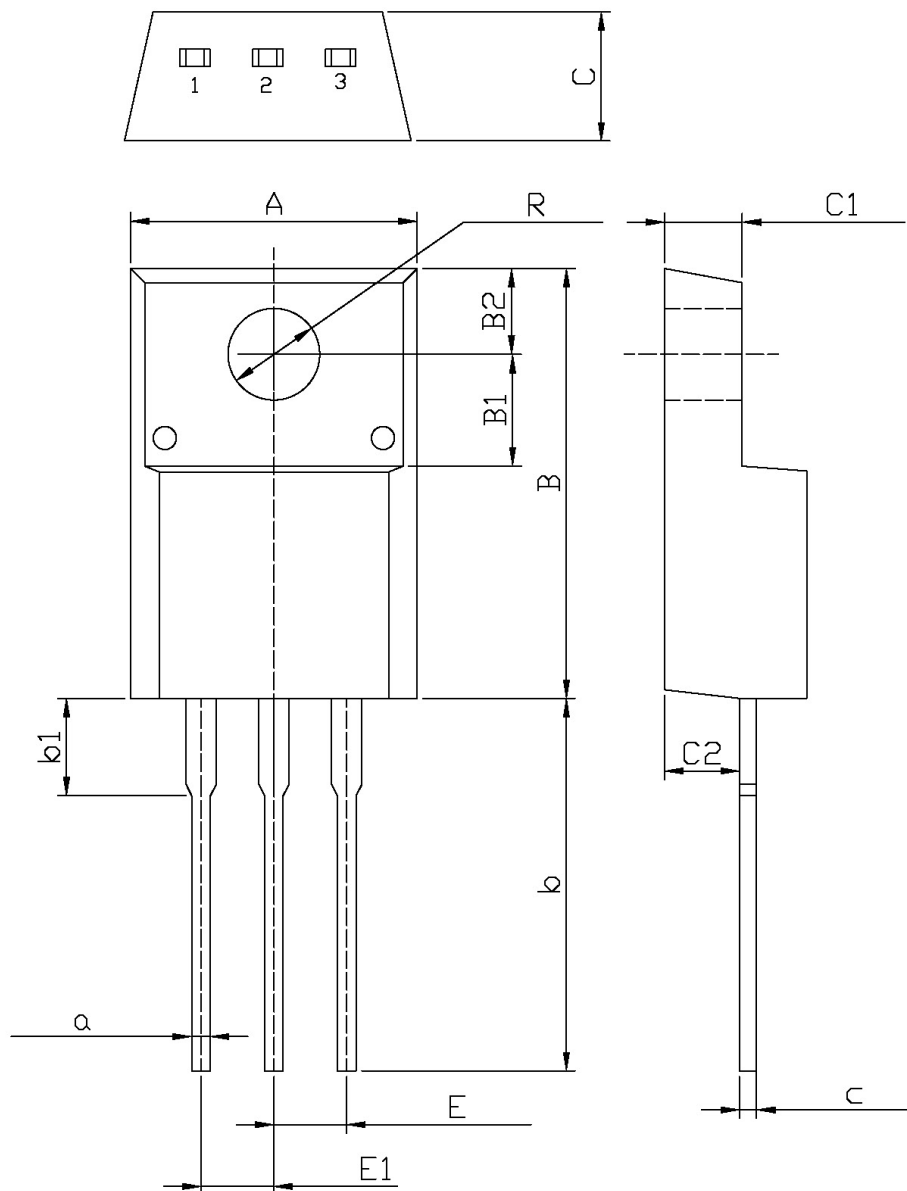
电参数曲线图 / Electrical Characteristic Curve



外形尺寸图 / Package Dimensions

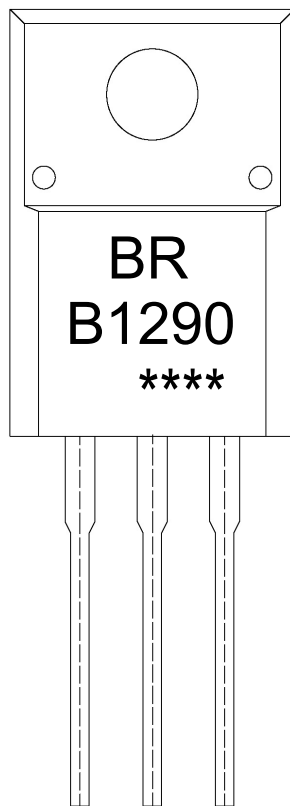
T□-220F

单位: mm



Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
C	4.3	4.7	b1	2.9	3.9
A	9.7	10.3	a	0.55	0.75
B	14.7	15.3	E	2.29	2.79
B1	3.8	4.0	E1	2.29	2.79
B2	2.9	3.1	C1	2.5	2.9
R	3.0	3.4	C2	2.5	2.7
b	12.5	13.5	c	0.5	0.7

印章说明 / Marking Instructions



说明：

BR： 为公司代码

B1290： 为型号代码

****： 为生产批号代码，随生产批号变化。

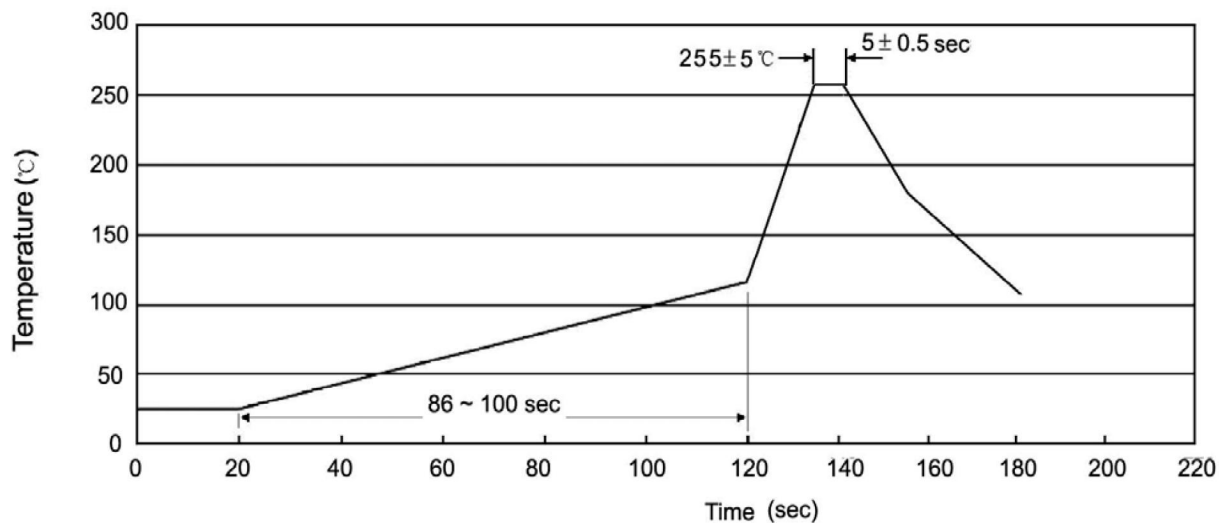
Note:

BR: Company Code.

B1290: Product Type.

****: Lot No. Code, code change with Lot No.

波峰焊温度曲线图(无铅) / Temperature Profile for Dip Soldering(Pb-Free)



说明：

1. 预热温度 25 ~ 150°C，时间 60 ~ 90sec;
2. 峰值温度 255±5°C，时间持续为 5±0.5sec;
3. 焊接制程冷却速度为 2 ~ 10°C/sec.

Note:

1. Preheating: 25~150°C, Time: 60~90sec.
2. Peak Temp.: 255±5°C, Duration: 5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：270±5°C

时间：10±1 sec.

Temp.: 270±5°C

Time: 10±1 sec

包装规格 / Packaging SPEC.

散件包装 / BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Bag 只/袋	Bags/Inner Box 袋/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Bag 袋	Inner Box 盒	Outer Box 箱
TO-220/F	200	10	2,000	5	10,000	135×190	237×172×102	560×245×195

套管包装 / TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-220/F	50	20	1,000	5	5,000	532×31.4×5.5	555×164×50	575×290×180

使用说明 / Notices